

25V PNP MEDIUM POWER TRANSISTOR IN SOT223

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BVcEo > -25V
- Ic = -3A High Continuous Current
- Icm = -8A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -300mV @ -1A
- Complementary NPN Type: DIODES™ FZT649
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ FZT749Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

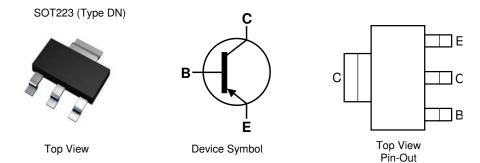
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.112 grams (Approximate)

Applications

MOSFET and IGBT gate driving



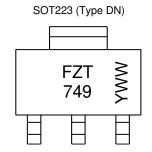
Ordering Information (Note 4)

Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
Fait Nullibei	Fackage	Walking	neer Size (Iliches)	rape widin (iiiii)	Qty.	Carrier
FZT749QTA	SOT223 (Type DN)	FZT749	7	12	1,000	Reel
FZT749QTC	SOT223 (Type DN)	FZT749	13	12	4,000	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



FZT749 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2 = 2022) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	-35	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	VEBO	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	Ісм	-8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)		2.0	W	
Fower Dissipation	(Note 7)	P _D	1.6	VV	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	р	62.5		
mermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		Rejl	12.9		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

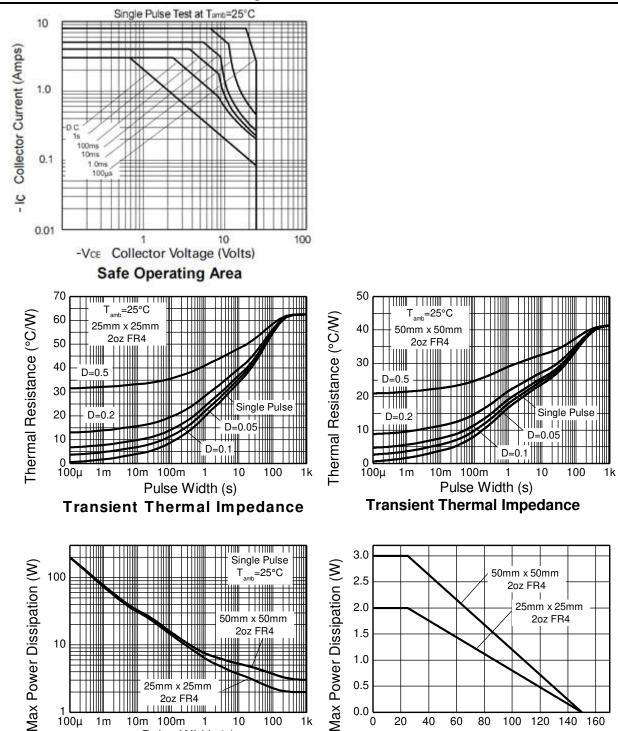
Notes:

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



Pulse Width (s)

Pulse Power Dissipation

100 120 140 160

80

Temperature (°C)

Derating Curve

60

20



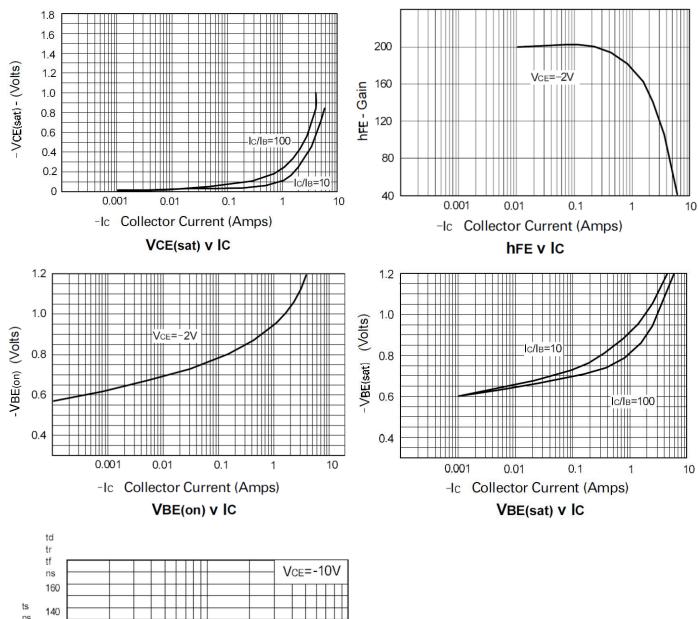
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

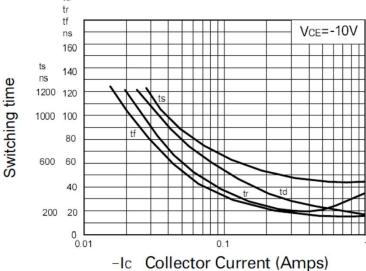
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	ВУсво	-35	_	_	V	$I_C = -100\mu A$	
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-25	_	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA	
Callactor Cut Off Current		_	1	-100	nA	V _{CB} = -30V	
Collector Cut-Off Current	Ісво	_	_	-10	μΑ	V _{CB} = -30V, T _A = +100°C	
Emitter Cut-Off Current	I _{EBO}	_	1	-100	nA	V _{EB} = -5.6V	
Callanter Franklar Catronation Valtage (Nata 11)		_	-0.12	-0.3	.,	Ic = -1A, I _B = -100mA	
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	-0.40	-0.6	V	Ic = -3A, I _B = -300mA	
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	-0.9	-1.25	V	Ic = -1A, I _B = -100mA	
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	-0.8	-1.0	V	Ic = -1A, VcE = -2V	
	hFE	70	200	_		Ic = -50mA, VcE = -2V	
DC Current Coin (Note 11)		100	200	300		Ic = -1A, VcE = -2V	
DC Current Gain (Note 11)		75	570	_	-	Ic = -2A, VcE = -2V	
		15	50	_		Ic = -6A, VcE = -2V	
Current Gain-Bandwidth Product (Note 11)	f _T	100	160	_	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz	
Turn-On Time	ton	_	40	_	ns	Vcc = -10V, Ic = -500mA,	
Turn-Off Time	toff	_	450	_	ns	$I_{B1} = -I_{B2} = -50mA$	
Output Capacitance	Cobo		55	100	pF	V _{CB} = -10V, f = 1MHz	

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





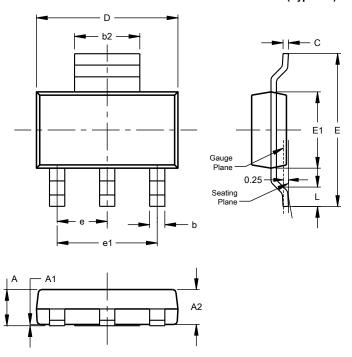
Switching Speeds



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

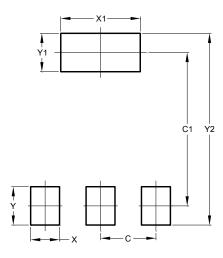


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Υ	1.60
Y1	1.60
V۵	9.00



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